

Features

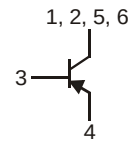
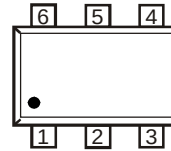
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DNLS160V)
- Surface Mount Package Suited for Automated Assembly
- Ultra Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 1)**
- **"Green Device" (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**



SOT-563

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.003 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-1	A
Peak Pulse Collector Current	I_{CM}	-2	A
Base Current (DC)	I_B	-300	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80	—	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	—	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	—	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	-100 -50	nA μA	V _{CB} = -60V, I _E = 0 V _{CB} = -60V, I _E = 0, T _A = 150°C
Collector Cutoff Current	I _{CES}	—	—	-100	nA	V _{CE} = -60V, V _{BE} = 0
Emitter Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V, I _C = 0
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h _{FE}	200 150 100	325 250 180	—	V	V _{CE} = -5V, I _C = -1mA V _{CE} = -5V, I _C = -500mA V _{CE} = -5V, I _C = -1A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	— — —	-90 -90 -160	-160 -175 -330	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	—	160	330	mΩ	I _C = -1A, I _B = -100mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-0.95	-1.1	V	I _C = -1A, I _B = -50mA
Base-Emitter Turn On Voltage	V _{BE(ON)}	—	-0.82	-0.9	V	V _{CE} = -5V, I _C = -1A
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	10	15	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	150	220	—	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	—	36	—	ns	V _{CC} = -10V I _C = -0.5A, I _{B1} = I _{B2} = -25mA
Delay Time	t _d	—	12	—	ns	
Rise Time	t _r	—	24	—	ns	
Turn-Off Time	t _{off}	—	163	—	ns	
Storage Time	t _s	—	132	—	ns	
Fall Time	t _f	—	31	—	ns	

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

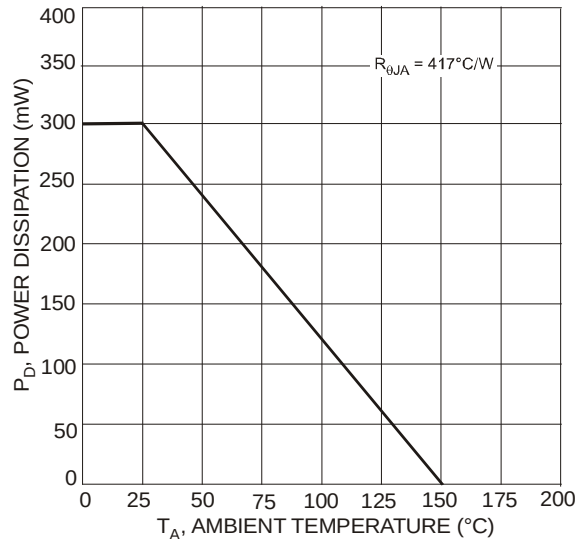


Fig. 1 Maximum Power Dissipation vs. Ambient Temperature

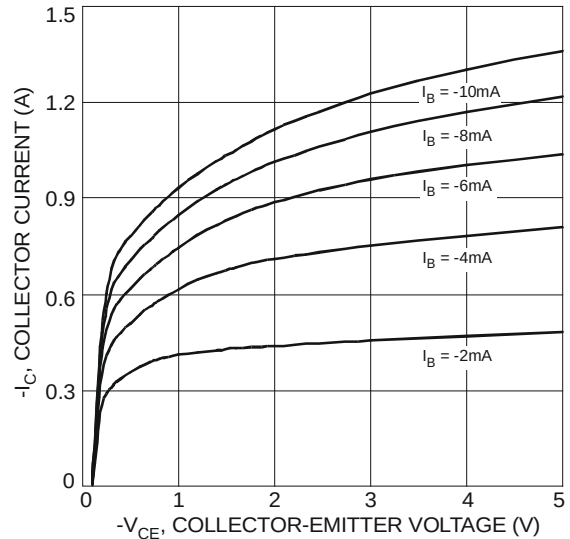


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

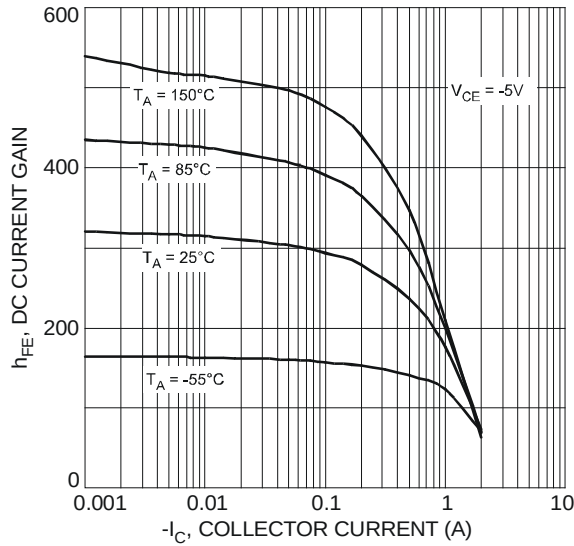


Fig. 3 Typical DC Current Gain vs. Collector Current

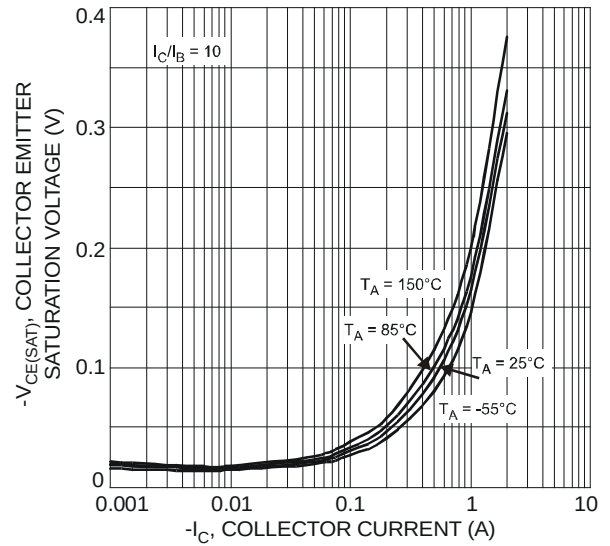


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

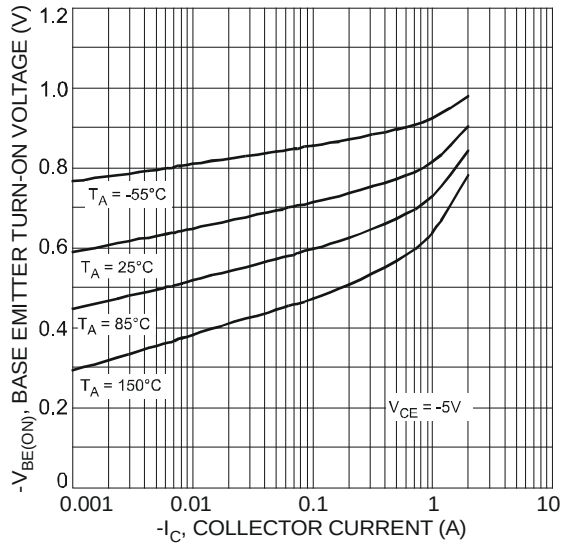


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current

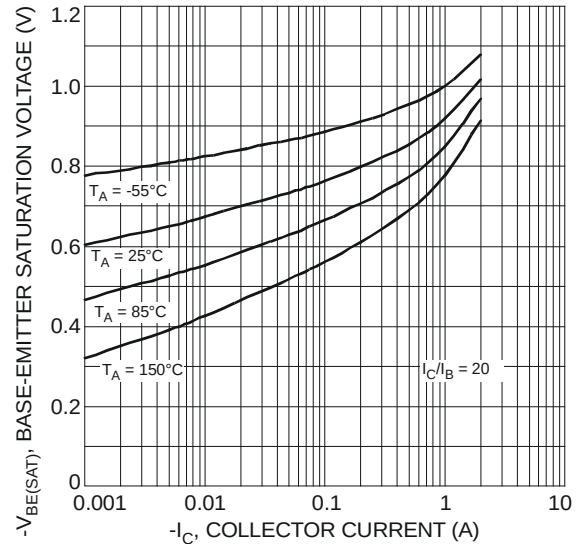


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

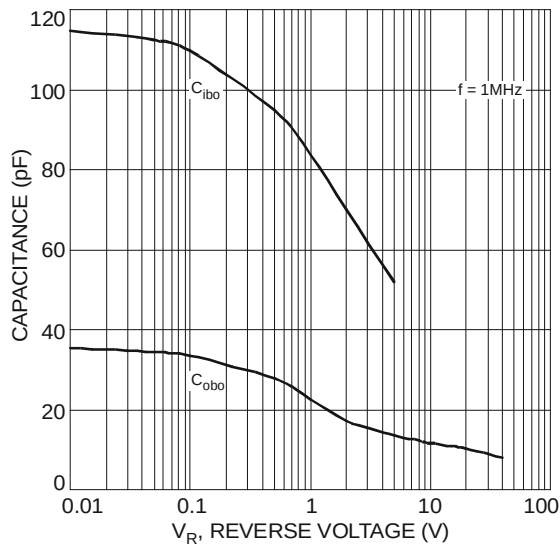


Fig. 7 Typical Total Capacitance

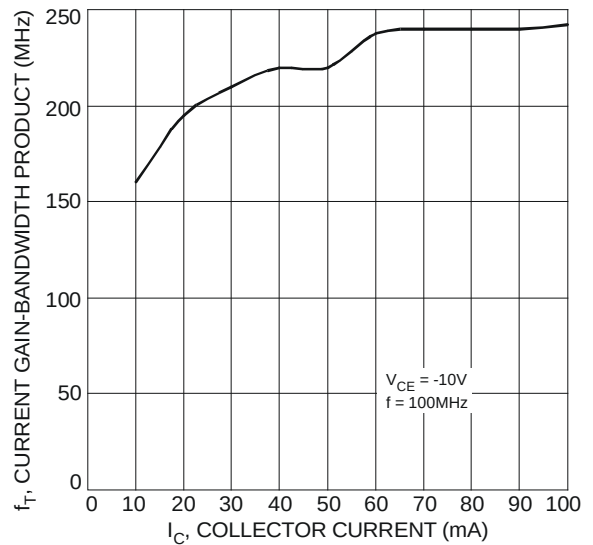


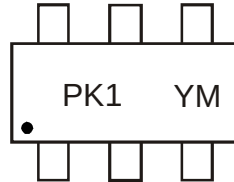
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DPLS160V-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



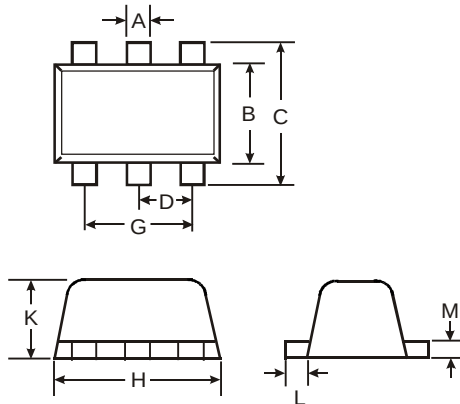
PK1 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: V = 2008
M = Month ex: 9 = September

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

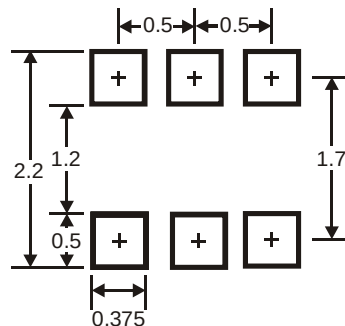
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout (in mm)



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